



32K × 8 HIGH SPEED CMOS STATIC RAM

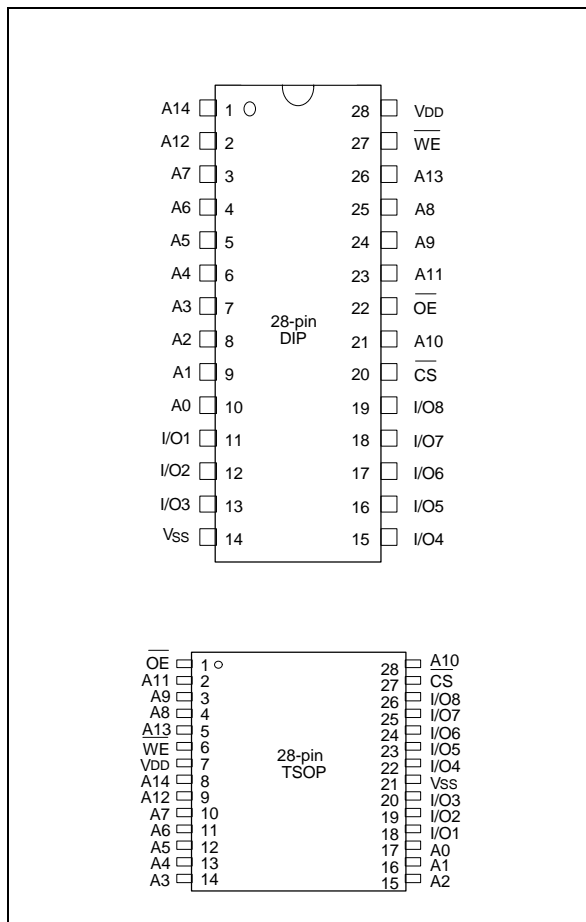
GENERAL DESCRIPTION

The W24257AC is a high speed, low power CMOS static RAM organized as 32768 × 8 bits that operates on a single 5-volt power supply. This device is manufactured using Winbond's high performance CMOS technology.

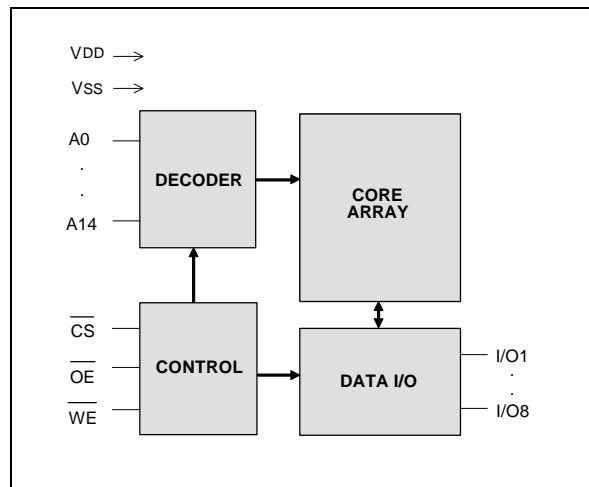
FEATURES

- High speed access time: 10/12/15/20 nS (max.)
- Low power consumption:
 - Active: 400 mW (typ.)
- Single +5V power supply
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three-state outputs
- Available packages: 28-pin 300 mil SOJ, 330 mil SOP, skinny DIP and standard type one TSOP (8 mm × 13.4 mm)

PIN CONFIGURATIONS



BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0–A14	Address Inputs
I/O1–I/O8	Data Inputs/Outputs
CS	Chip Select Input
WE	Write Enable Input
OE	Output Enable Input
VDD	Power Supply
VSS	Ground



DC CHARACTERISTICS

Absolute Maximum Ratings

PARAMETER	RATING	UNIT
Supply Voltage to Vss Potential	-0.5 to +7.0	V
Input/Output to Vss Potential	-0.5 to VDD +0.5	V
Allowable Power Dissipation	1.0	W
Storage Temperature	-65 to +150	°C
Operating Temperature	0 to +70	°C

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

TRUTH TABLE

\overline{CS}	\overline{OE}	\overline{WE}	MODE	I/O1 - I/O8	VDD CURRENT
H	X	X	Not Selected	High Z	ISB, ISB1
L	H	H	Output Disable	High Z	IDD
L	L	H	Read	Data Out	IDD
L	X	L	Write	Data In	IDD

OPERATING CHARACTERISTICS

(VDD = 5V ±10%, VSS = 0V, TA = 0 to 70° C)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Input Low Voltage	VIL	-	-0.5	-	+0.8	V	
Input High Voltage	VIH	-	+2.2	-	VDD +0.5	V	
Input Leakage Current	ILI	VIN = VSS to VDD	-10	-	+10	μA	
Output Leakage Current	ILO	V _{I/O} = VSS to VDD, \overline{CS} = VIH or \overline{OE} = VIH or \overline{WE} = VIL	-10	-	+10	μA	
Output Low Voltage	VOL	IOL = +8.0 mA	-	-	0.4	V	
Output High Voltage	VOH	IOH = -4.0 mA	2.4	-	-	V	
Operating Power Supply Current	IDD	\overline{CS} = VIL, I/O = 0 mA Cycle = MIN. Duty = 100%	10	-	-	170	mA
			12	-	-	160	mA
			15	-	-	150	mA
			20	-	-	140	mA
Standby Power Supply Current	ISB	\overline{CS} = VIH Cycle = MIN., Duty = 100%	-	-	30	mA	
	ISB1	\overline{CS} ≥ VDD -0.2V	-	-	10	mA	

Note: Typical characteristics are at VDD = 5V, TA = 25° C.

CAPACITANCE

(V_{DD} = 5V, T_A = 25° C, f = 1 MHz)

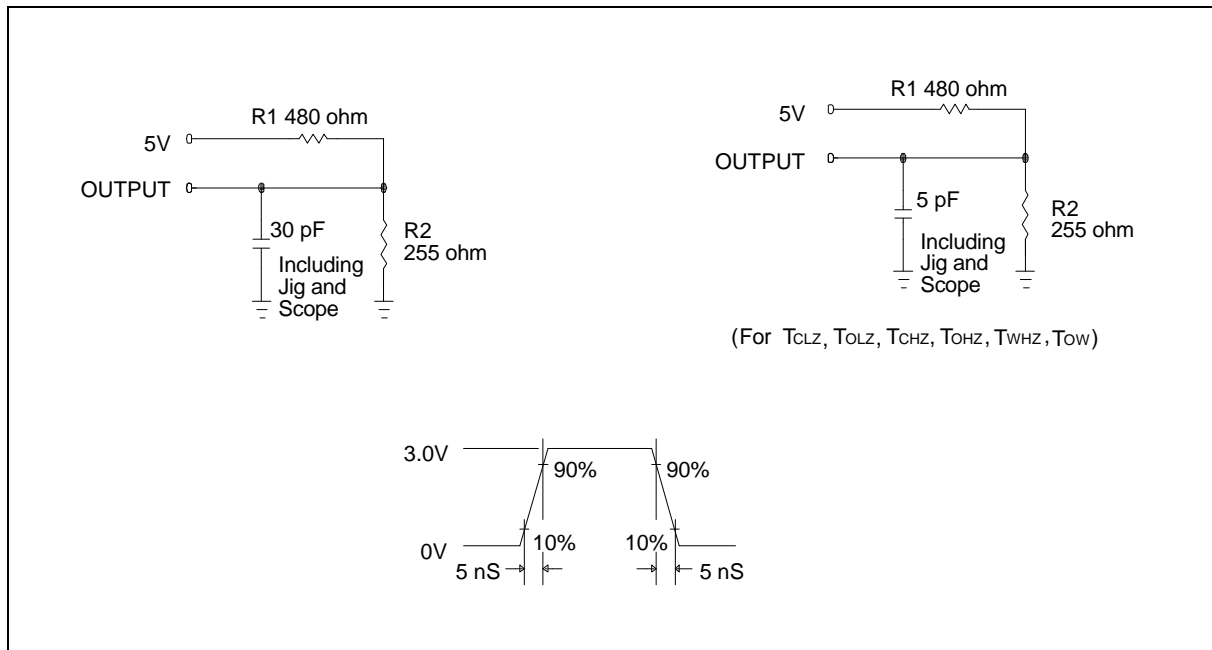
PARAMETER	SYM.	CONDITIONS	MAX.	UNIT
Input Capacitance	C _{IN}	V _{IN} = 0V	8	pF
Input/Output Capacitance	C _{I/O}	V _{OUT} = 0V	10	pF

Note: These parameters are sampled but not 100% tested.

AC TEST CONDITIONS

PARAMETER	CONDITIONS
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	5 nS
Input and Output Timing Reference Level	1.5V
Output Load	C _L = 30 pF, I _{OH} /I _{OL} = -4 mA/8 mA

AC TEST LOADS AND WAVEFORM



AC CHARACTERISTICS

(V_{DD} = 5V ±10%, V_{SS} = 0V, T_A = 0 to 70° C)

Read Cycle

PARAMETER	SYM.	W24257AC-10		W24257AC-12		W24257AC-15		W24257AC-20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	T _{RC}	10	-	12	-	15	-	20	-	nS
Address Access Time	T _{AA}	-	10	-	12	-	15	-	20	nS
Chip Select Access Time	T _{ACS}	-	10	-	12	-	15	-	20	nS
Output Enable to Output Valid	T _{AOE}	-	5	-	6	-	7	-	10	nS
Chip Selection to Output in Low Z	T _{CLZ} *	3	-	3	-	3	-	3	-	nS
Output Enable to Output in Low Z	T _{OLZ} *	0	-	0	-	0	-	0	-	nS
Chip Deselection to Output in High Z	T _{CHZ} *	-	5	-	6	-	7	-	10	nS
Output Disable to Output in High Z	T _{OHZ} *	-	5	-	6	-	7	-	10	nS
Output Hold from Address Change	T _{OH}	3	-	3	-	3	-	3	-	nS

* These parameters are sampled but not 100% tested.

Write Cycle

PARAMETER		SYM.	W24257AC-10		W24257AC-12		W24257AC-15		W24257AC-20		UNIT
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time		T _{WC}	10	-	12	-	15	-	20	-	nS
Chip Selection to End of Write		T _{CW}	9	-	10	-	13	-	17	-	nS
Address Valid to End of Write		T _{AW}	9	-	10	-	13	-	17	-	nS
Address Setup Time		T _{AS}	0	-	0	-	0	-	0	-	nS
Write Pulse Width		T _{WP}	9	-	10	-	10	-	12	-	nS
Write Recovery Time	\overline{CS} , \overline{WE}	T _{WR}	0	-	0	-	0	-	0	-	nS
Data Valid to End of Write		T _{DW}	6	-	7	-	9	-	10	-	nS
Data Hold from End of Write		T _{DH}	0	-	0	-	0	-	0	-	nS
Write to Output in High Z		T _{WHZ} *	-	6	-	7	-	8	-	10	nS
Output Disable to Output in High Z		T _{OHZ} *	-	6	-	7	-	8	-	10	nS
Output Active from End of Write		T _{OW}	0	-	0	-	0	-	0	-	nS

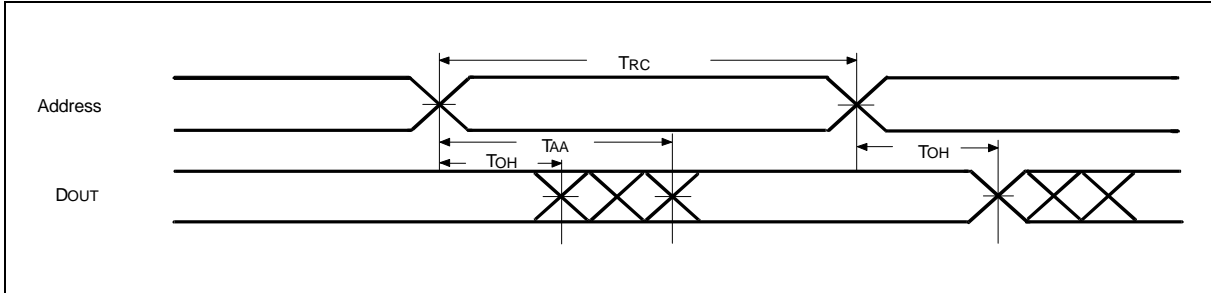
* These parameters are sampled but not 100% tested.



TIMING WAVEFORMS

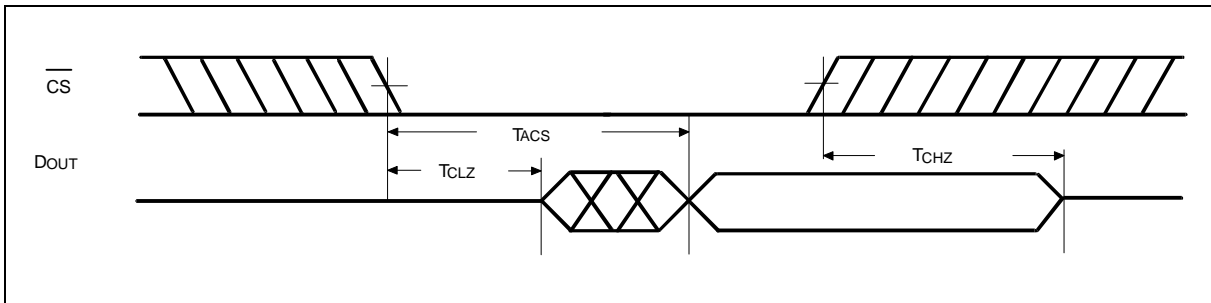
Read Cycle 1

(Address Controlled)



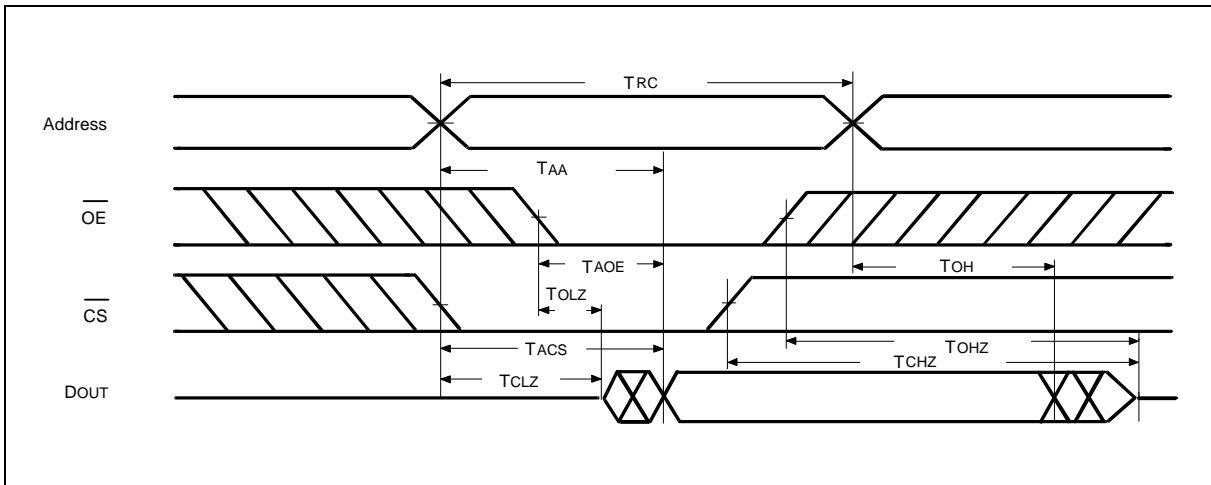
Read Cycle 2

(Chip Select Controlled)



Read Cycle 3

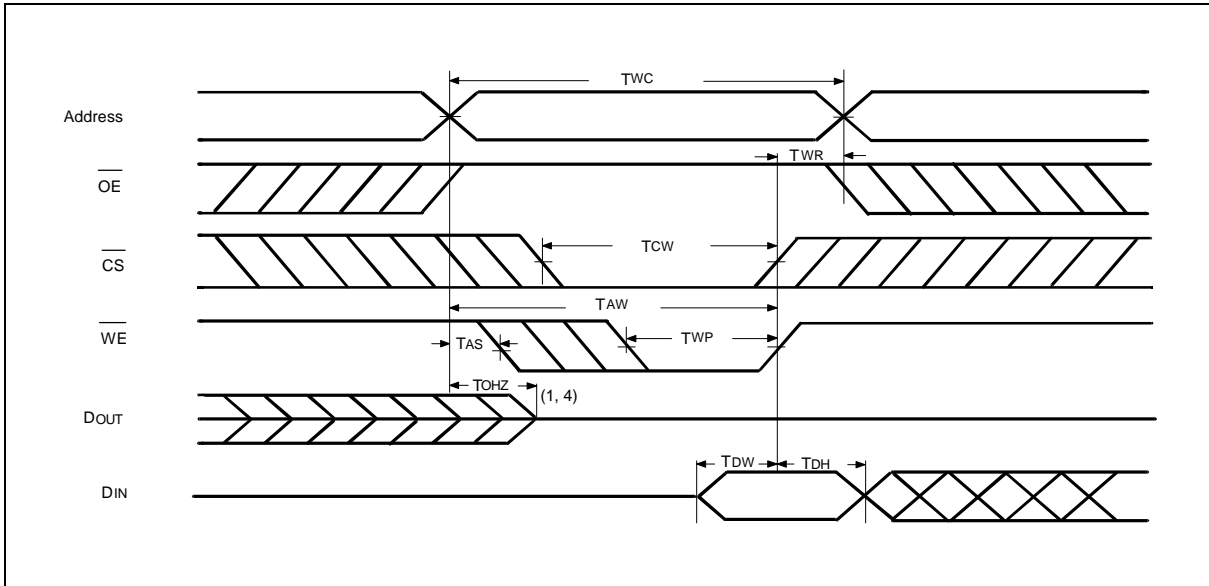
(Output Enable Controlled)



Timing Waveforms, continued

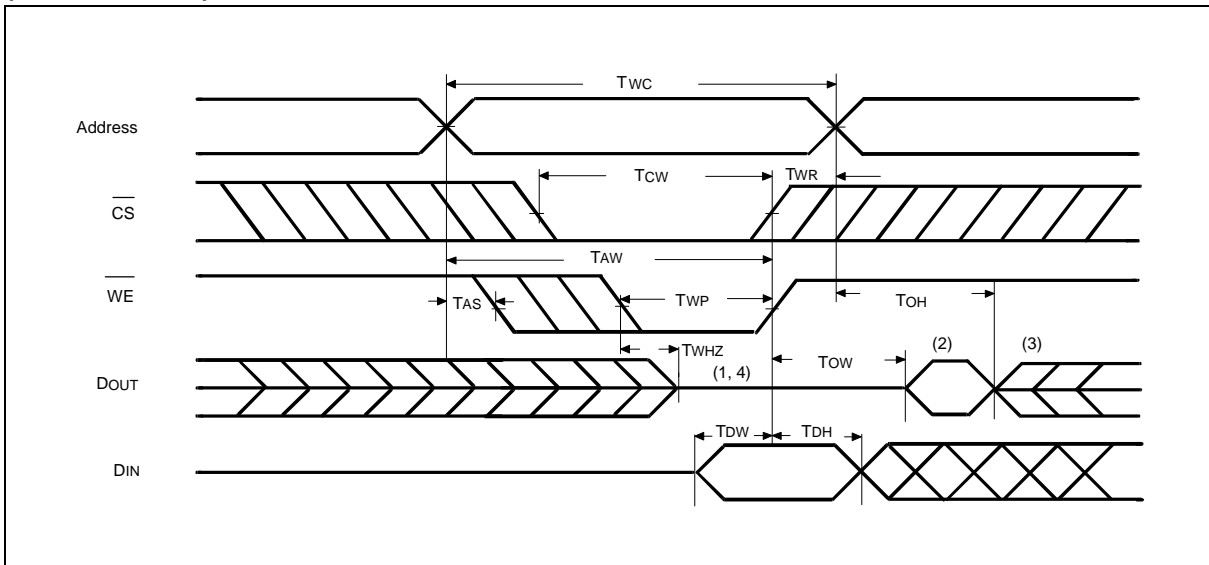
Write Cycle 1

(\overline{OE} Clock)



Write Cycle 2

($\overline{OE} = V_{IL}$ Fixed)



Notes:

1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
2. The data output from DOUT are the same as the data written to DIN during the write cycle.
3. DOUT provides the read data for the next address.
4. Transition is measured ± 500 mV from steady state with $C_L = 5$ pF. This parameter is guaranteed but not 100% tested.



ORDERING INFORMATION

PART NO.	ACCESS TIME (nS)	OPERATING CURRENT MAX. (mA)	STANDBY CURRENT MAX. (mA)	PACKAGE
W24257ACK-10	10	170	10	300 mil skinny DIP
W24257ACK-12	12	160	10	300 mil skinny DIP
W24257ACK-15	15	150	10	300 mil skinny DIP
W24257ACK-20	20	140	10	300 mil skinny DIP
W24257ACJ-10	10	170	10	300 mil SOJ
W24257ACJ-12	12	160	10	300 mil SOJ
W24257ACJ-15	15	150	10	300 mil SOJ
W24257ACJ-20	20	140	10	300 mil SOJ
W24257ACS-10	10	170	10	330 mil SOP
W24257ACS-12	12	160	10	330 mil SOP
W24257ACS-15	15	150	10	330 mil SOP
W24257ACS-20	20	140	10	330 mil SOP
W24257ACQ-10	10	170	10	Standard type one TSOP
W24257ACQ-12	12	160	10	Standard type one TSOP
W24257ACQ-15	15	150	10	Standard type one TSOP
W24257ACQ-20	20	140	10	Standard type one TSOP

Notes:

1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

PACKAGE DIMENSIONS

28-pin P-DIP Skinny

Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.175	—	—	4.45
A ₁	0.010	—	—	0.25	—	—
A ₂	0.125	0.130	0.135	3.18	3.30	3.43
B	0.016	0.018	0.022	0.41	0.46	0.56
B ₁	0.058	0.060	0.064	1.47	1.52	1.63
C	0.008	0.010	0.014	0.20	0.25	0.36
D	—	1.388	1.400	—	35.26	35.56
E	0.300	0.310	0.320	7.62	7.87	8.13
E ₁	0.283	0.288	0.293	7.19	7.32	7.44
e ₁	0.090	0.100	0.110	2.29	2.54	2.79
L	0.120	0.130	0.140	3.05	3.30	3.56
a	0°	—	15°	0°	—	15°
e _A	0.330	0.350	0.370	8.38	8.89	9.40
S	—	—	0.055	—	—	1.40

Notes:

- Dimensions D Max. & S include mold flash or tie bar burrs.
- Dimension E₁ does not include interlead flash.
- Dimensions D & E₁ include mold mismatch and are determined at the mold parting line.
- Dimension B₁ does not include dambar protrusion/intrusion.
- Controlling dimension: Inches.
- General appearance spec. should be based on final visual inspection spec.

28-pin Small Outline J Band

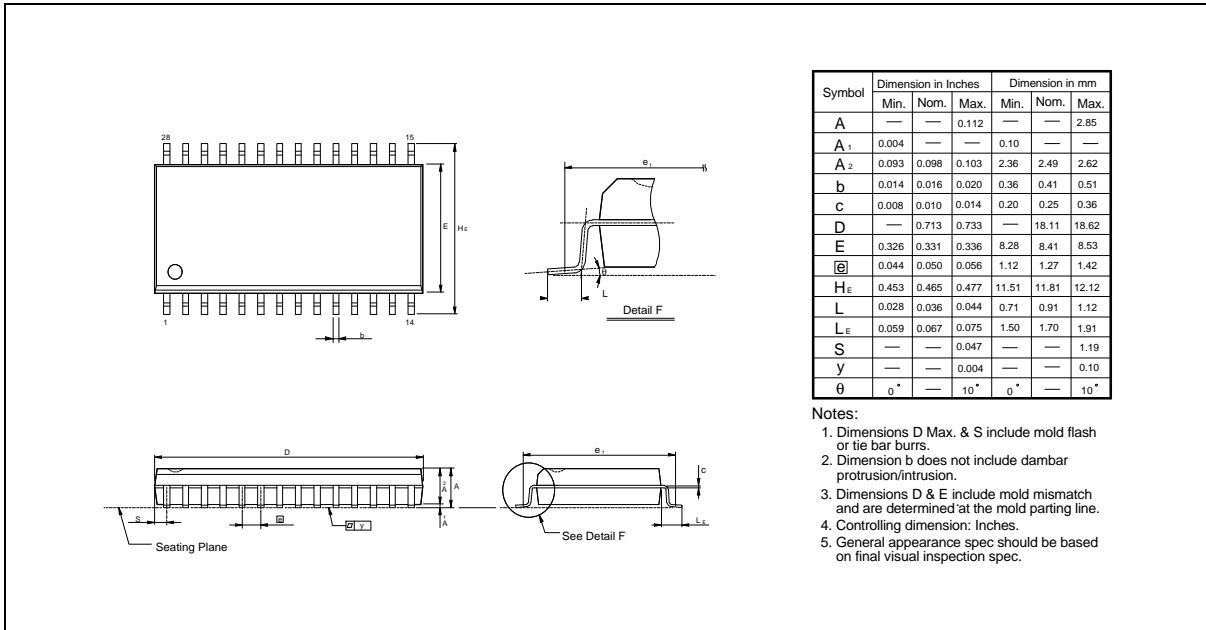
Symbol	Dimension in Inches			Dimension in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	—	—	0.140	—	—	3.56
A ₁	0.027	—	—	0.69	—	—
A ₂	0.095	0.100	0.105	2.41	2.54	2.67
b ₁	0.026	0.028	0.032	0.66	0.71	0.81
b	0.016	0.018	0.022	0.41	0.46	0.56
c	0.008	0.010	0.014	0.20	0.25	0.36
D	—	0.710	0.730	—	18.03	18.54
E	0.295	0.300	0.305	7.49	7.62	7.75
⊕	0.044	0.050	0.056	1.12	1.27	1.42
e ₁	0.245	0.265	0.285	6.22	6.73	7.24
H _E	0.327	0.337	0.347	8.31	8.56	8.81
L	0.077	0.087	0.097	1.96	2.21	2.46
S	—	—	0.045	—	—	1.14
y	—	—	0.004	—	—	0.10
θ	0°	—	10°	0°	—	10°

Notes:

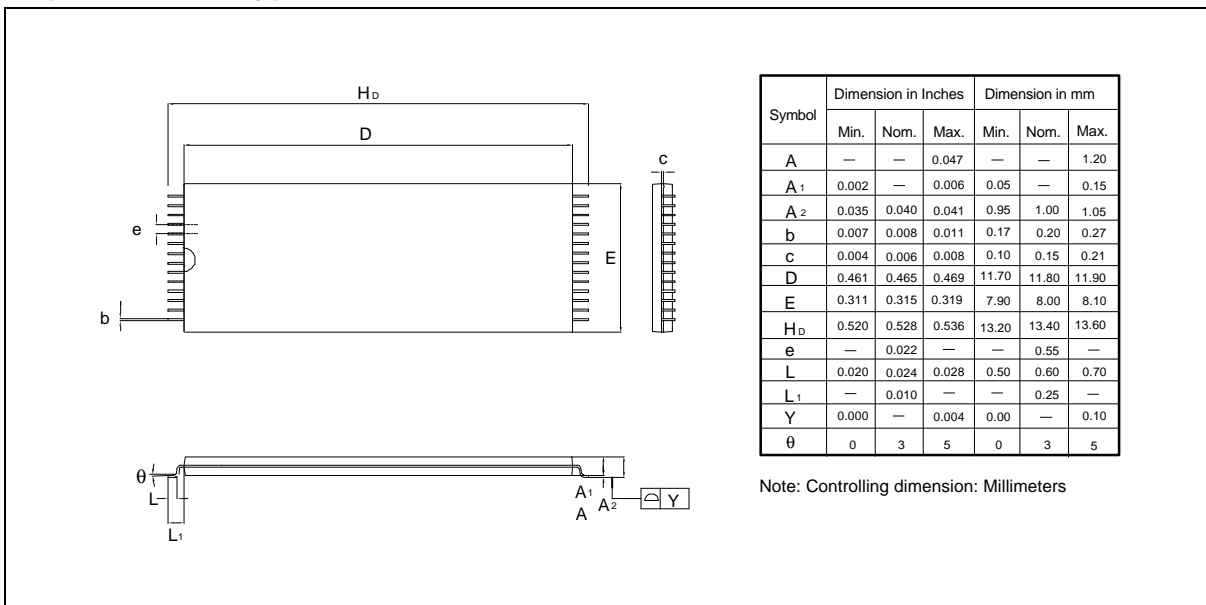
- Dimensions D Max. & S include mold flash or tie bar burrs.
- Dimension b does not include dambar protrusion/intrusion.
- Dimensions D & E include mold mismatch and are determined at the mold parting line.
- Controlling dimension: Inches.
- General appearance spec. should be based on final visual inspection spec.

Package Dimensions, continued

28-pin SO Wide Body



28-pin Standard Type One TSOP





VERSION HISTORY

VERSION	DATE	PAGE	DESCRIPTION
A1	Oct. 1998		Initial Issued



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Note: All data and specifications are subject to change without notice.